

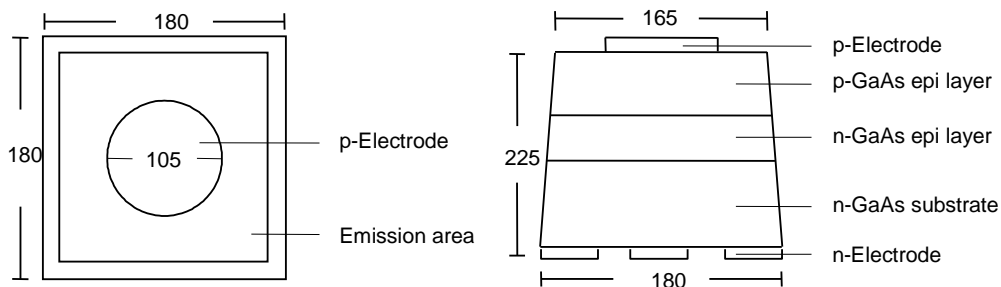
■ Features :

- GaAs/GaAs Wafer
- Good Spectral Matched to Si Detector

■ Typical Applications :

- Peripheral Device
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	180 μm x 180 μm
	Thickness	225 μm
	Emission area	165 μm
	Bonding pad	105 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Rough	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.26	1.50	V
		$I_F = 100 \text{ mA}$	-	1.48	1.90	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.50	-	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

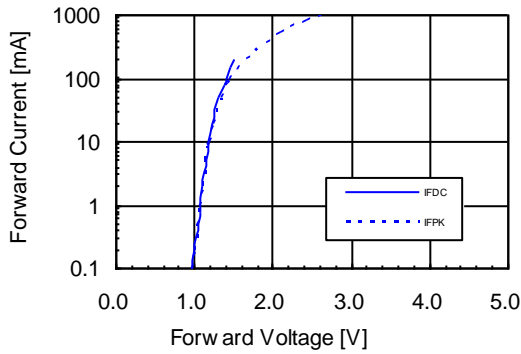


Fig 2. Relative Radiant Power vs. Wavelength

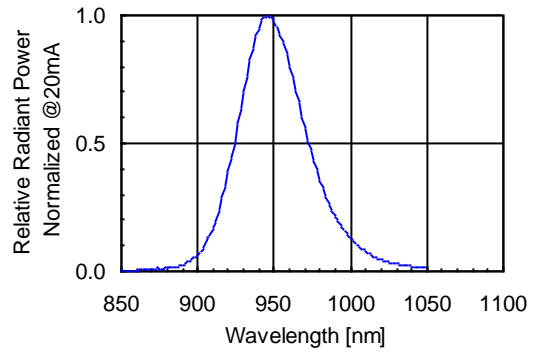


Fig 3. Relative Radiant Power vs. Forward DC Current

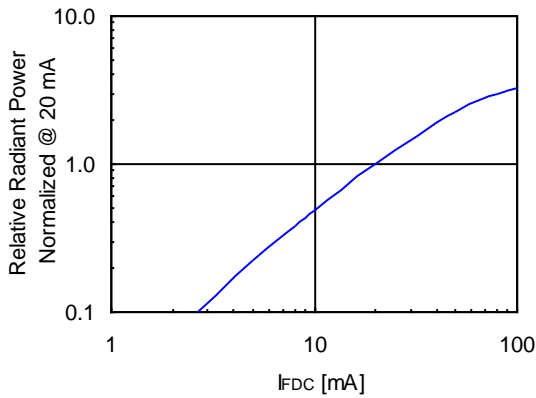


Fig 4. Relative Radiant Power vs. Forward Peak Current

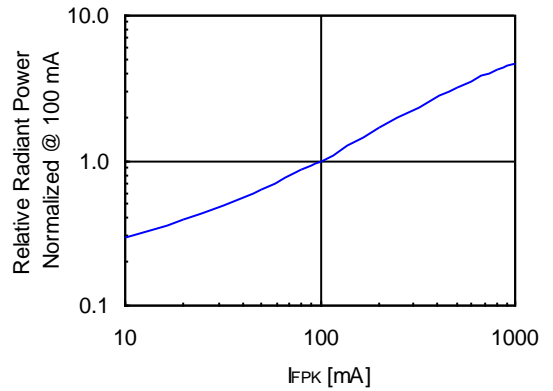


Fig 5. Forward DC Voltage vs. Temperature

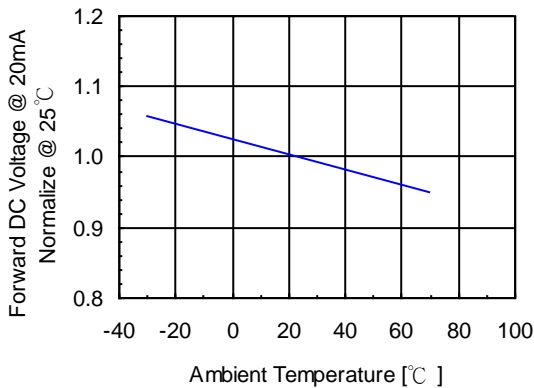


Fig 6. Relative Radiant Power vs. Temperature

